

CORRECTION

[View Article Online](#)
[View Journal](#) | [View Issue](#)

Cite this: *J. Mater. Chem. C*, 2021, 9, 9713

Correction: Charge transfer doping with an organic layer to achieve a high-performance p-type WSe₂ transistorMinho Yoon^a and Jiyoul Lee^{*ab}

DOI: 10.1039/d1tc90150h

Correction for 'Charge transfer doping with an organic layer to achieve a high-performance p-type WSe₂ transistor' by Minho Yoon *et al.*, *J. Mater. Chem. C*, 2021, DOI: 10.1039/D1TC01780B.

rsc.li/materials-c

The authors regret an error in Fig. 1 of the published article, where Fig. 1(d) was replaced with a copy of Fig. 1(c). The corrected form of Fig. 1 is shown below:

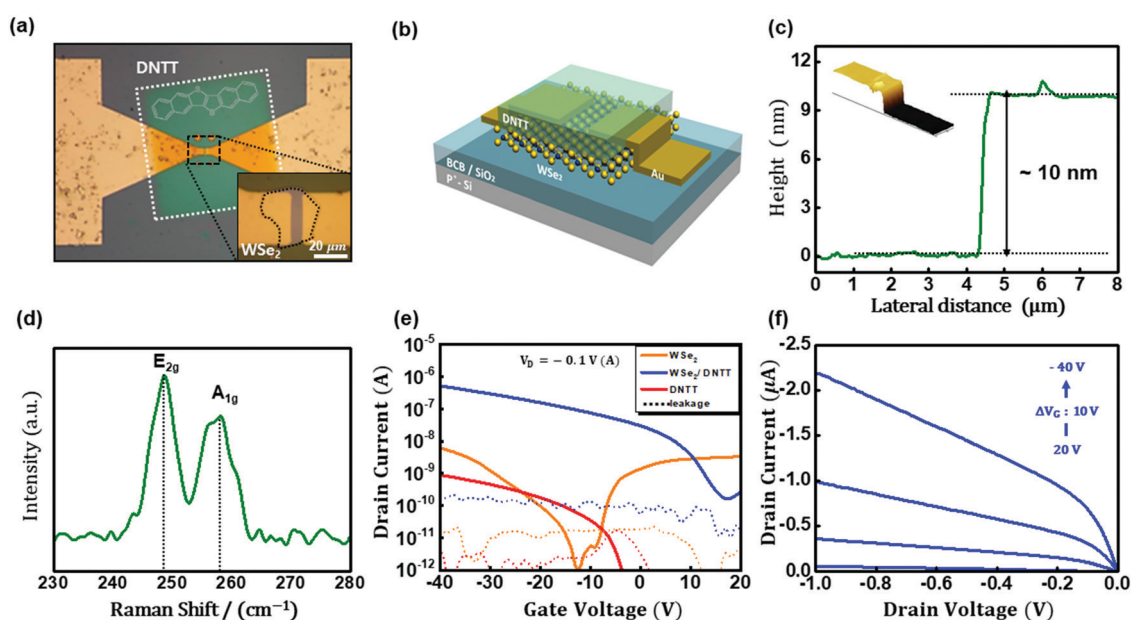


Fig. 1 (a) Optical micrograph of the WSe₂/dinaphtho[2,3-*b*:2',3'-*f*]thieno[3,2-*b*]thiophene (DNTT) field-effect transistor (FET), along with Au source (S)/drain (D) electrodes; the green square region is patterned DNTT, and the inset shows a magnified S/D region over the WSe₂ FET channel. (b) Three-dimensional schematics of the WSe₂/DNTT FET on a hydrophobic benzocyclobutene (BCB) (300 nm)/SiO₂ (285 nm) dielectric support. (c) Atomic force microscopy image and thickness profile (~10 nm) of the WSe₂ FET channel. (d) Raman spectrum of the WSe₂ flake, before DNTT deposition; the peaks near 250 and 257 cm⁻¹ correspond to the in-plane (E_{2g}) and out-of-plane (A_{1g}) vibrational modes, respectively. (e) Transfer characteristics of DNTT and the WSe₂ FET before and after DNTT deposition. (f) Output characteristics of the WSe₂/DNTT FET.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a Department of Smart Green Technology Engineering, Pukyong National University, Busan, 48547, Korea. E-mail: jiyoul_lee@pknu.ac.kr

^b Department of Nanotechnology Engineering, Pukyong National University, Busan, 48547, Korea